

Supporting Information

Influence of Cu doping on the visible-light-induced photocatalytic activity of InVO₄

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Materials characterization

The interplanar spacing (d_{hkl}) values of all samples were calculated from (112) plane as shown in Table S1. The interplanar spacing of (112) orthorhombic crystallographic plane of 0.5-5.0 mol% Cu-doped InVO_4 increased compared with pure InVO_4 , implying that Cu^{2+} ions are substituted into orthorhombic InVO_4 lattice.

Table S1 d_{hkl} -spacing at (112) plane of pure InVO_4 and 0.5-5.0 mol% Cu-doped InVO_4

Samples	2θ	θ	$\sin\theta$	λ (nm)	d_{hkl} (nm)
Pure InVO_4	33.175	16.588	0.2854	0.1540	0.2697
0.5Cu- InVO_4	33.070	16.535	0.2846	0.1540	0.2706
1.0Cu- InVO_4	33.055	16.528	0.2845	0.1540	0.2707
2.0Cu- InVO_4	33.085	16.529	0.2845	0.1540	0.2707
5.0Cu- InVO_4	33.070	16.535	0.2846	0.1540	0.2706